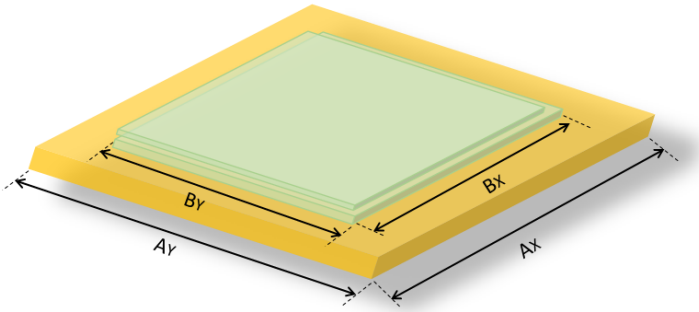
FESD3V3A

Chip TVS Diode



Mechanical Data	Notes
Dice size	AX/AY:450um,BX/BY:310um
Wafer size	4”(Gross die:79500pcs/Good die>73935)
Chip Thickness	A)230um±20um
Scribe line width	60um
Top metal	Al
Back side metal	Ti-Ni-Ag for soldering

Parameter	Symbol	Conditions	Value	Unit
Reverse stand-off voltage	VRWM		4.0	V
Peak pulse power	PPP	Tp=8/20us	300**	W
Peak pulse current	IPP	Tp=8/20us	28**	A
Electrostatic discharge	VESD	IEC61000-4-2 Level 4	± 15(AIR) ± 8(Contact)	KV
Max.junction temp.	Tj		+150	℃

Characteristics TA=25℃

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Breakdown voltage	VBR	IT=1mA	5.2	5.8	6.3	V
Reverse leakage current	IR	VR=3.3V			15.0	uA
Clamping voltage	VC	IPP=1A IPP=5A			6.9 8.4	V
Diode capacitance	Cj	VR=0V f=1MHz			350	pf

Notes:

(1)sampling testing:no bad dice inking/guaranteed good die >93%

(2)100% testing

(3)Tj=Ta+Rth(j-a)*(pf+pr),where Rth(j-a)-thermal resistance,Pf-forward power dissipation, Pr-revers power dissipation

(4)**For device testing